

L Number	Hits	Search Text	DB	Time stamp
1	670259	resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 16:15
7	602	(resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) with (bi-layer bilayer bi adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 16:55
33	40	((resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) with (bi-layer bilayer bi adj layer)) with (si silicon si-contain\$3 silicon-contain\$3) with (top upper)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 17:18
41	16	((resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) with (bi-layer bilayer bi adj layer)) with (si silicon si-contain\$3 silicon-contain\$3) with (top upper)) and (cleav\$4 generator pag!)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 17:20
47	5	((resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) with (bi-layer bilayer bi adj layer)) with (si silicon si-contain\$3 silicon-contain\$3) with (top upper)) and (cleav\$4) and (generator pag!) and (acrylate methacrylate hydroxystyrene olefin silylethoxy)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 17:24
53	4	((("5985524") or ("6444408")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 17:25
59	4	((("5985524") or ("6444408")).PN.) and organic	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 17:26
65	2	((("5985524") or ("6444408")).PN.) and (e-beam ebeam e adj beam electromagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 17:27
71	2	((("5985524") or ("6444408")).PN.) and (x-ray xray x adj ray)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 17:28
77	10486	plasma near3 reduc\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 17:31
83	253	(plasma near3 reduc\$3) with (n2 nitrogen "n.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 17:32
89	109	(plasma near3 reduc\$3) with (n2 nitrogen "n.sub.2") with (hydrogen h2 "h.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 17:44
95	1	(plasma near3 reduc\$3) with (n2 nitrogen "n.sub.2") with (ethylene c2h4 "c.sub.2 h.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 17:44
101	10	(plasma near3 reduc\$3) with (ethylene c2h4 "c.sub.2 h.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 17:44
107	0	(plasma near3 reduc\$3) with (n2 nitrogen "n.sub.2") with ((hydrogen h2 "h.sub.2") near2 generat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 17:46

113	0	(plasma near3 reduc\$3) with (n2 nitrogen "n.sub.2") with (hydrogen-generat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 17:46
119	10	(plasma near3 reduc\$3) with ((hydrogen h2 "h.sub.2") near2 generat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 17:47
125	1	(plasma near3 reduc\$3) with (hydrogen-generat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 17:47
131	675	((hydrogen h2 "h.sub.2") near2 generat\$4) hydrogen-generat\$4) with (ammonia nh3 "nh.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 17:49
137	49	((hydrogen h2 "h.sub.2") near2 generat\$4) hydrogen-generat\$4) with (ammonia nh3 "nh.sub.3") with plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 17:49
-	12	MAHOROWALA-.in. MAHOROWALA-ARPAN-P-.in. MAHOROWALA-ARPAN-PRAVIN-.in. MAHOROWALA-A-P-.in. MAHOROWARA-.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:05
-	670259	resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 16:12
-	381880	(organic polymer polymeric resin) near (layer underlayer under-layer film coating)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:09
-	17074	(resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) near3 (silicon si silicon-contain\$3 si-contain\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:09
-	526	treat\$3 near3 plasma near3 (ethylene hydrogen h2 "h.sub.2" c2h4 "c.sub.2 h.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:10
-	2	reduc\$3 with critical with dimension with (resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) with image with (bilayer bi-layer bi adj layer) etch\$4 near3 (so2 "so.sub.2" sulfur adj dioxide) near3 (oxygen o2 "o.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:14
-	26	etch\$4 near3 (so2 "so.sub.2" sulfur adj dioxide) near3 (oxygen o2 "o.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:17
-	13	(resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) and ((organic polymer polymeric resin) near (layer underlayer under-layer film coating)) and (etch\$4 near3 (so2 "so.sub.2" sulfur adj dioxide) near3 (oxygen o2 "o.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:25
-	6	((resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) near3 (silicon si silicon-contain\$3 si-contain\$3)) and ((resist photoresist photo-resist photosensitive (sensitive near (photo light energy radiation))) and ((organic polymer polymeric resin) near (layer underlayer under-layer film coating)) and (etch\$4 near3 (so2 "so.sub.2" sulfur adj dioxide) near3 (oxygen o2 "o.sub.2"))))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:26

	346	((organic polymer polymeric resin) near (layer underlayer under-layer film coating)) with ((resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) near3 (silicon si silicon-contain\$3 si-contain\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:27
	0	((organic polymer polymeric resin) near (layer underlayer under-layer film coating)) with ((resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) near3 (silicon si silicon-contain\$3 si-contain\$3))) same (treat\$3 near3 plasma near3 (ethylene hydrogen h2 "h.sub.2" c2h4 "c.sub.2 h.sub.4"))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:27
	4	((organic polymer polymeric resin) near (layer underlayer under-layer film coating)) with ((resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) near3 (silicon si silicon-contain\$3 si-contain\$3))) and (treat\$3 near3 plasma near3 (ethylene hydrogen h2 "h.sub.2" c2h4 "c.sub.2 h.sub.4"))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:28
	1	((organic polymer polymeric resin) near (layer underlayer under-layer film coating)) with ((resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) near3 (silicon si silicon-contain\$3 si-contain\$3))) same (treat\$3 near3 plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:30
	18865	((organic polymer polymeric resin) near (layer underlayer under-layer film coating)) with (resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:29
	42	((organic polymer polymeric resin) near (layer underlayer under-layer film coating)) with (resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) same (treat\$3 near3 plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:37
	445	(resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) near3 (bilayer bi-layer bi adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:38
	0	((resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) near3 (bilayer bi-layer bi adj layer)) with etch\$4 with treat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:38
	3	((resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) near3 (bilayer bi-layer bi adj layer)) same etch\$4 same treat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:39
	18	((resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) near3 (bilayer bi-layer bi adj layer)) and (treat\$3 with plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:52
	13742	(resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) same etch\$3 same treat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:53

-	1800	(resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) same etch\$3 same (treat\$4 with plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:59
-	23	(resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) same etch\$3 same (treat\$3 near3 plasma near3 (ethylene hydrogen h2 "h.sub.2" c2h4 "c.sub.2 h.sub.4"))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 12:54
-	138	((resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) bilayer bi-layer bi adj layer) near2 etch\$3) with (treat\$4 near3 plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 13:09
-	60	((resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))) bilayer bi-layer bi adj layer) near2 etch\$3) with (treat\$4 near3 plasma) with remov\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 13:33
-	32747	plasma near3 (reduc\$3 chemical\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 13:36
-	163	plasma near3 (reduc\$3 near3 chemical\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 13:39
-	10	plasma near (reduc\$3 near chemical\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/28 15:38